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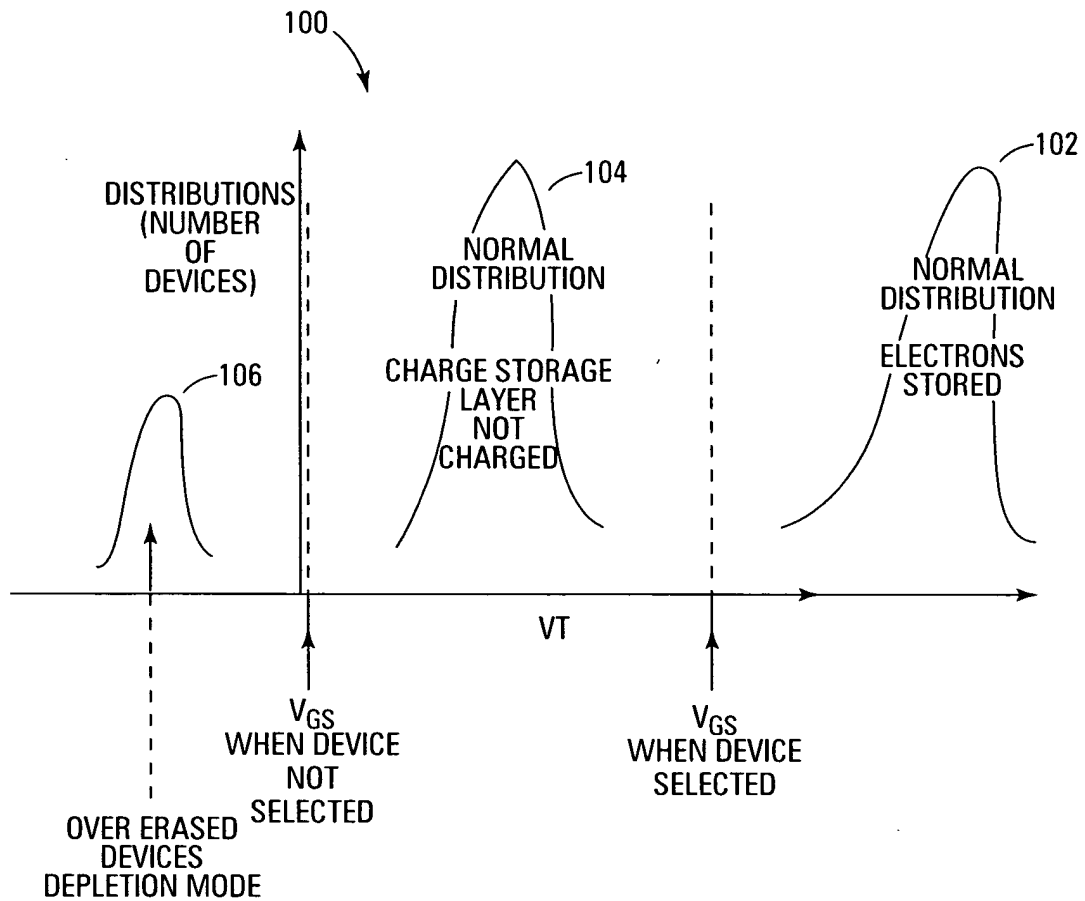


Fig. 1A

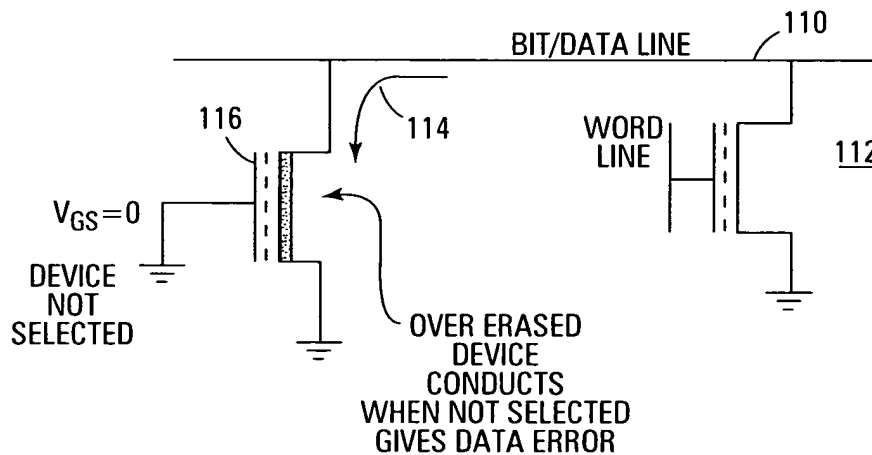


Fig. 1B

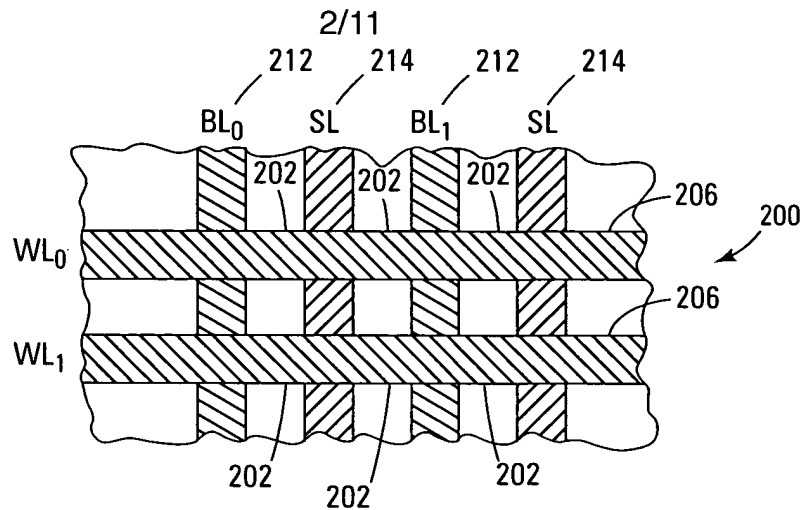


Fig. 2A
Prior Art

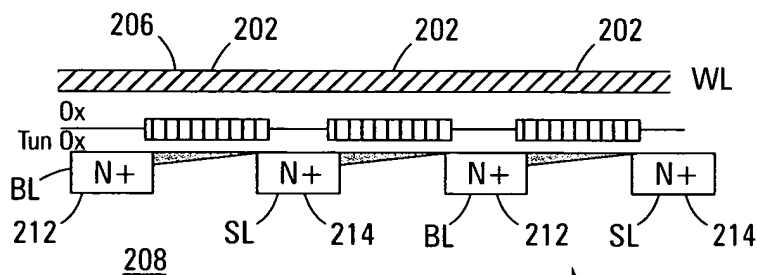


Fig. 2B
Prior Art

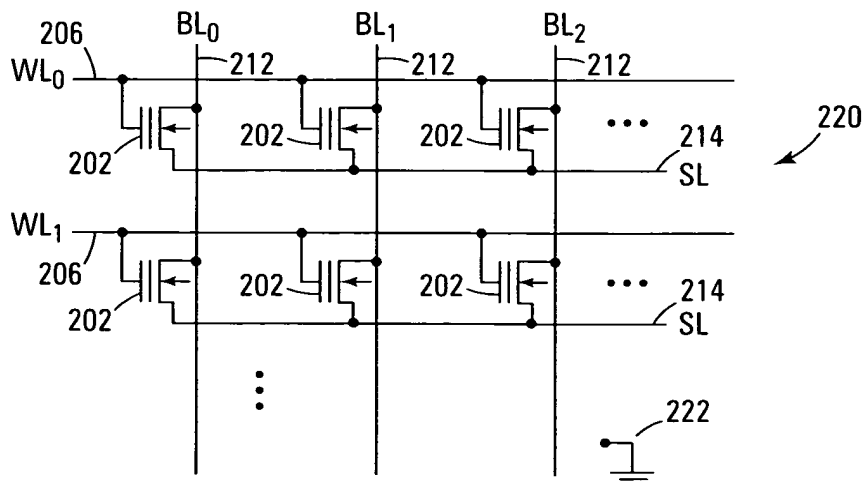
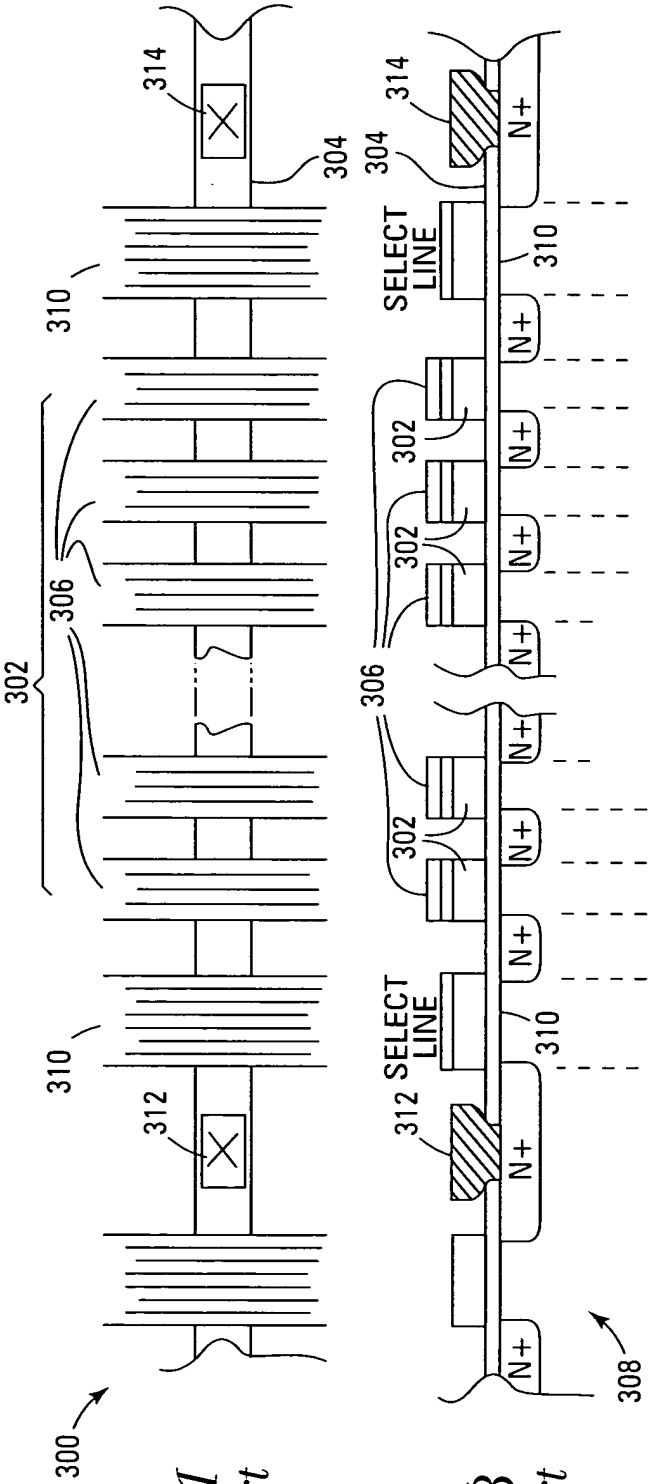


Fig. 2C
Prior Art



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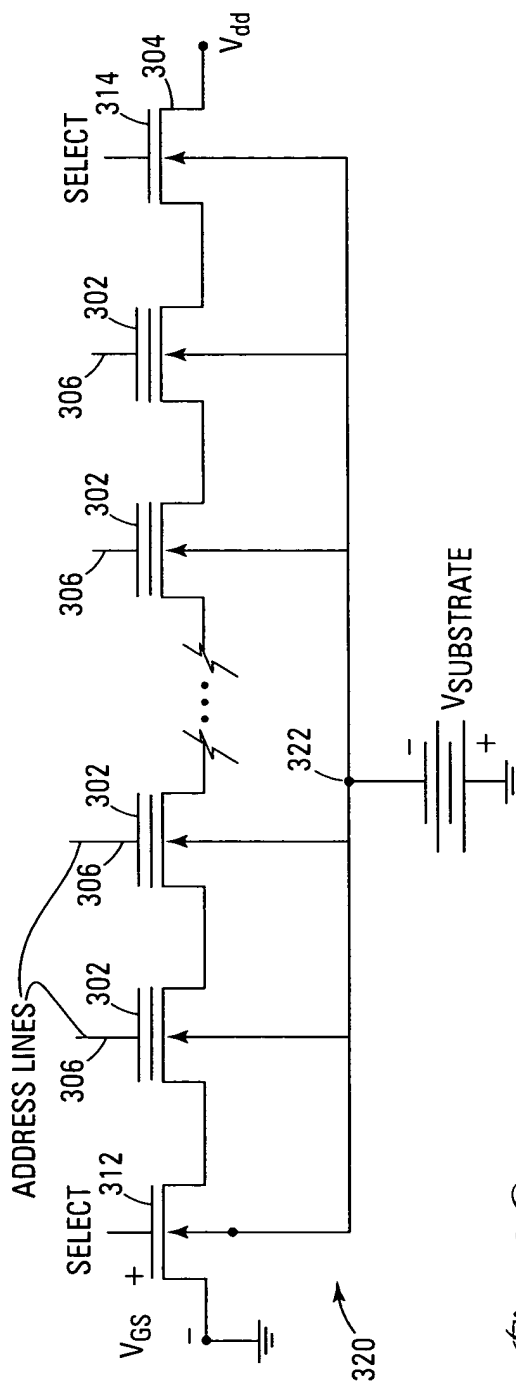


Fig. 3C
 Prior Art

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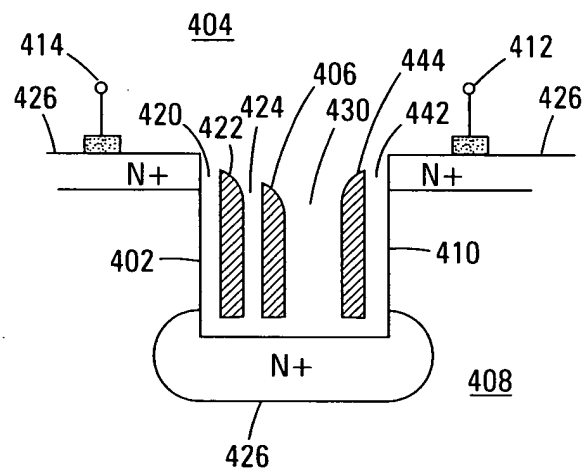


Fig. 4A

Fig. 4C

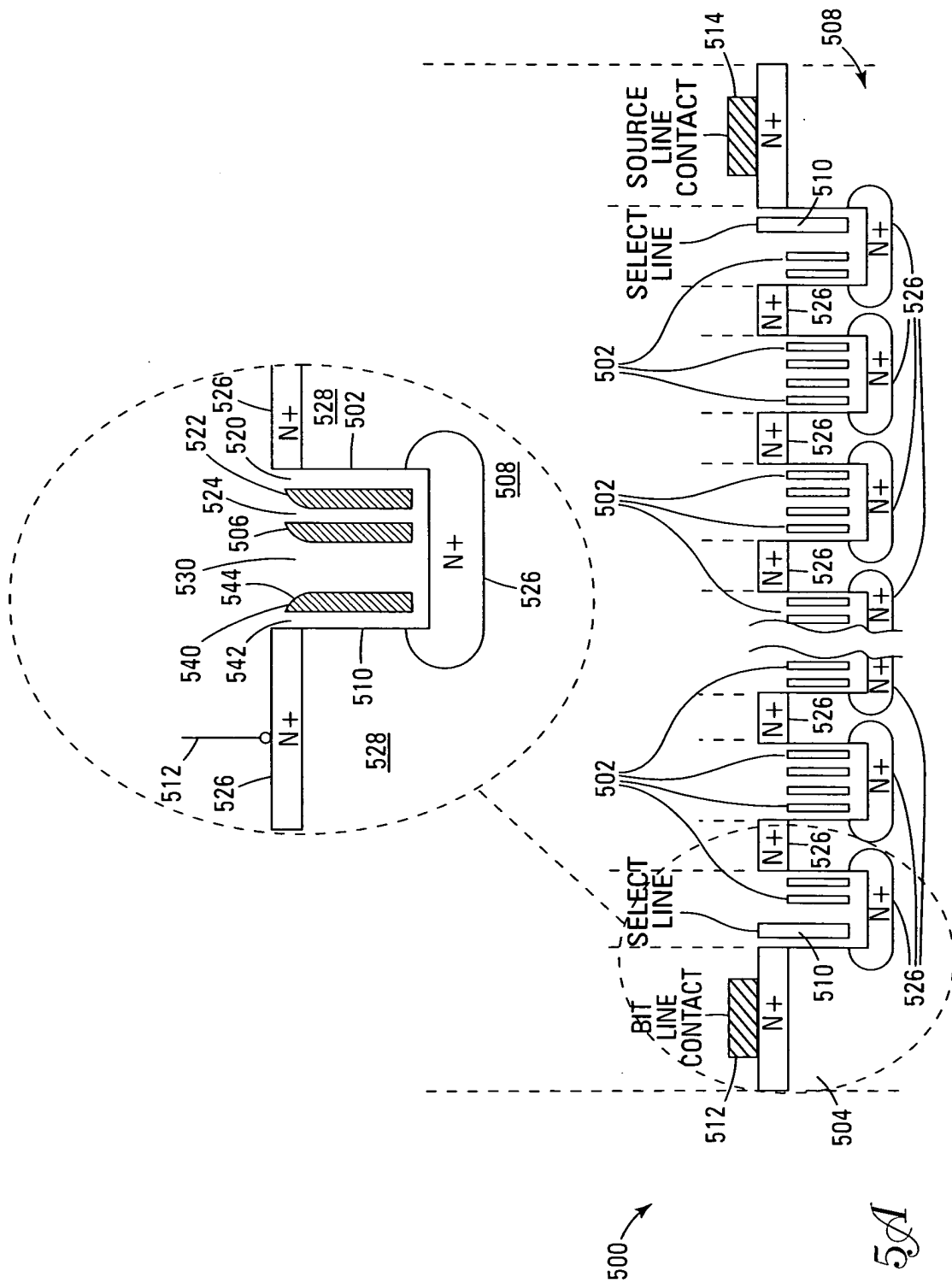


Fig. 5A

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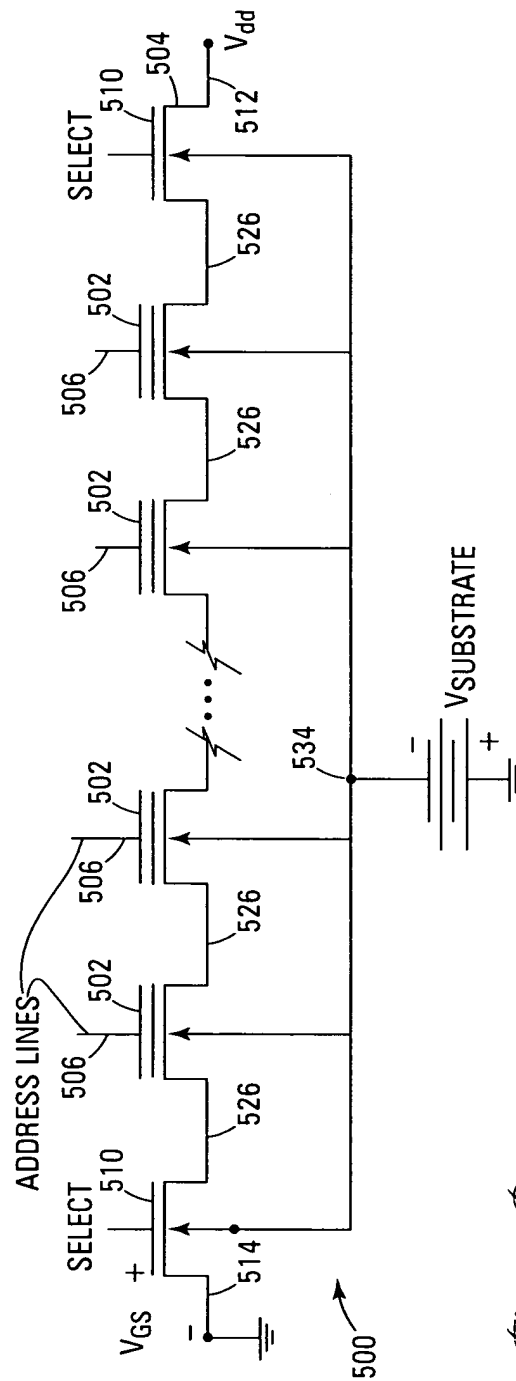


Fig. 5B

Fig. 5D

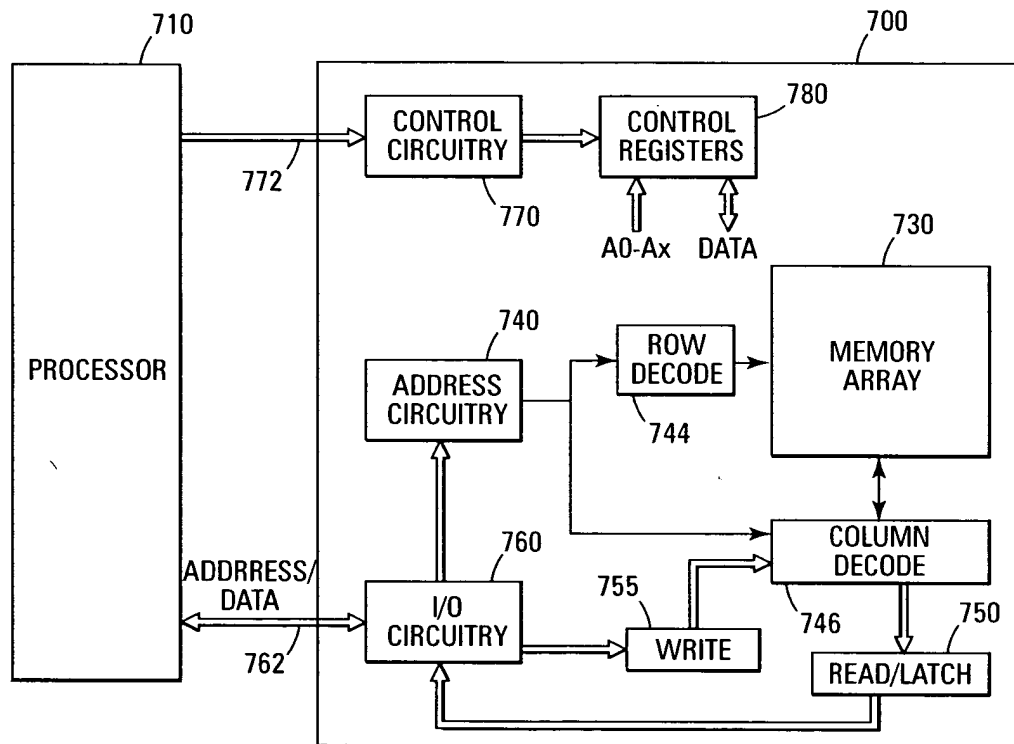
[illegible]

Fig. 6B

A 3D perspective view of a semiconductor device 600. It features three floating gates 608, each with a top surface 626 and side surfaces 628. The gates are separated by oxide regions 632. The device includes a substrate 604 and a gate stack 622. The floating gates are labeled with N+ regions. The device is shown in a perspective view, with the floating gates 608 and the gate stack 622 clearly visible. The substrate 604 is at the base, and the oxide regions 632 are between the gates. The gate stack 622 is on top of the floating gates. The N+ regions are on the top and side surfaces of the floating gates. The device is labeled with various reference numerals: 600, 604, 608, 622, 626, 628, 632, and N+.

Fig. 6C is a perspective view of a semiconductor device. It shows a series of memory cells arranged in a row. The device includes a substrate with N+ regions, oxide layers, and various conductive layers. Labels include 600, 602, 604, 606, 610, 620, 622, 624, 626, 628, 630, 632, 640, 642, 644, and 646. A bracket indicates "CONTROL/WRITE LINES" and another bracket indicates "SELECTED/READ LINES".

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Fig. 7